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| SANYO | No.3338 | 2SC4475 |
| | | NPN Triple Diffused Planar Silicon Transistor High-Voltage Amp, High-Voltage Switching Applications |

Applications

- High voltage amp
- High voltage switching
- Dynamic focus

Features

- High breakdown voltage ($V_{CEO\ min} = 1800V$)
- Small c_{ob} ($c_{ob\ typ} = 1.4pF$)
- Wide ASO
- High reliability (Adoption of HVP process)

Absolute Maximum Ratings at $T_a = 25^\circ C$

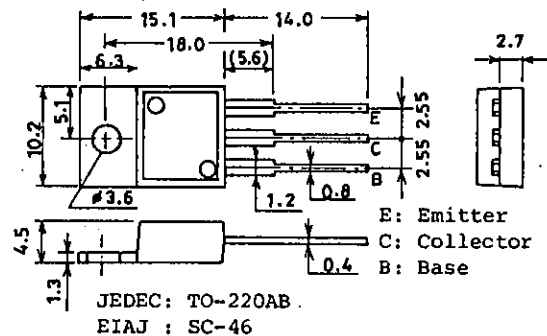
| | | | unit |
|------------------------------|-----------|-------------|------------|
| Collector-to-Base Voltage | V_{CBO} | 2000 | V |
| Collector-to-Emitter Voltage | V_{CEO} | 1800 | V |
| Emitter-to-Base Voltage | V_{EBO} | 5 | V |
| Collector Current | I_C | 3 | mA |
| Peak Collector Current | i_{cp} | 10 | mA |
| Collector Dissipation | P_C | 1.75 | W |
| Junction Temperature | T_j | 150 | $^\circ C$ |
| Storage Temperature | T_{stg} | -55 to +150 | $^\circ C$ |

Electrical Characteristics at $T_a = 25^\circ C$

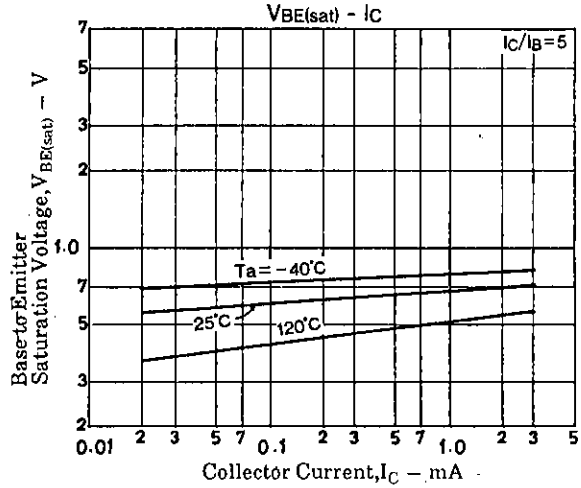
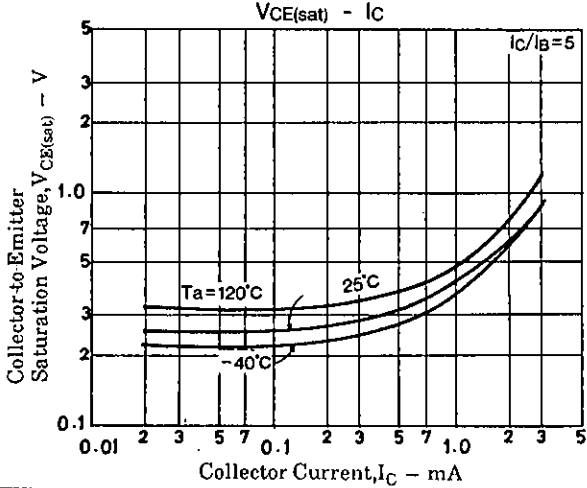
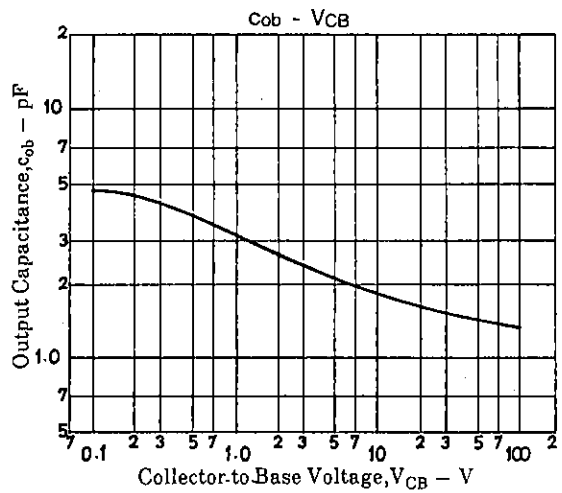
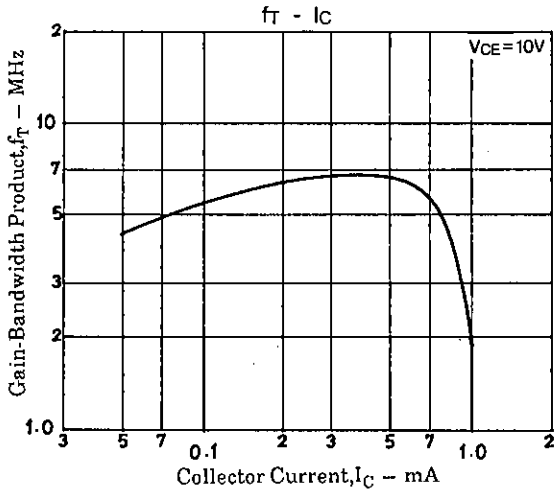
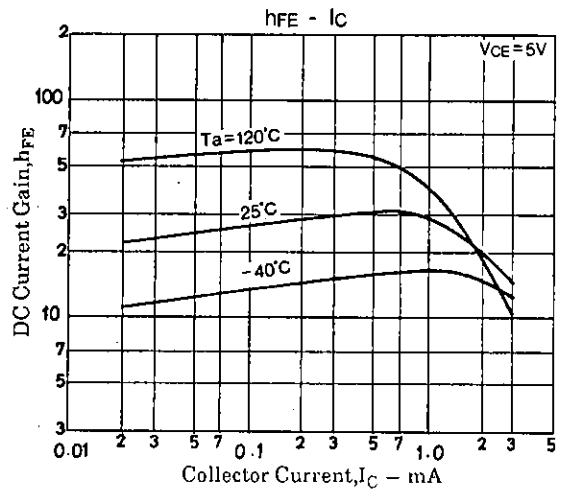
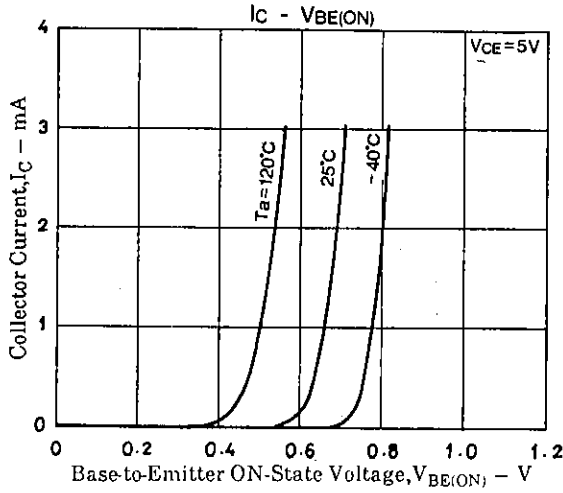
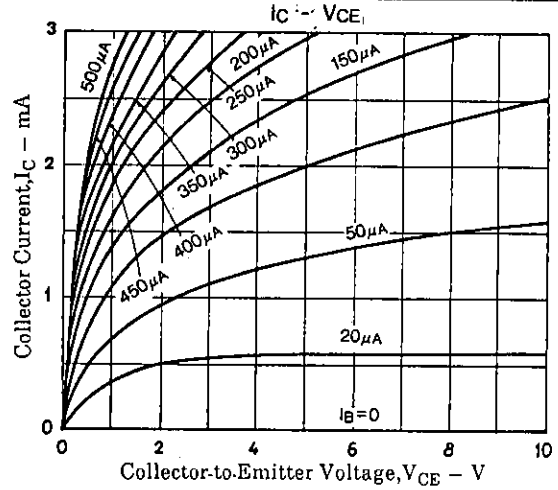
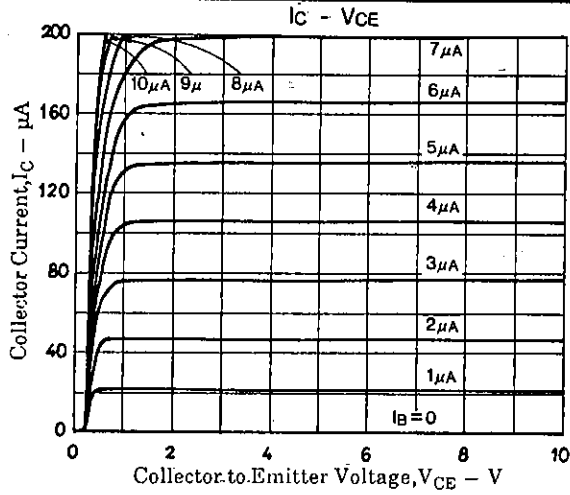
| | | | min | typ | max | unit |
|--------------------------|---------------|-----------------------------------|------|-----|-----|---------|
| Collector Cutoff Current | I_{CBO} | $V_{CB} = 1800V, I_E = 0$ | | | 1 | μA |
| Emitter Cutoff Current | I_{EBO} | $V_{EB} = 4V, I_C = 0$ | | | 1 | μA |
| DC Current Gain | h_{FE} | $V_{CE} = 5V, I_C = 100\mu A$ | 10 | | 60 | |
| Gain-Bandwidth Product | f_T | $V_{CE} = 10V, I_C = 200\mu A$ | | 6 | | MHz |
| C-E Saturation Voltage | $V_{CE(sat)}$ | $I_C = 200\mu A, I_B = 40\mu A$ | | | 5 | V |
| B-E Saturation Voltage | $V_{BE(sat)}$ | $I_C = 200\mu A, I_B = 40\mu A$ | | | 2 | V |
| C-B Breakdown Voltage | $V_{(BR)CBO}$ | $I_C = 10\mu A, I_E = 0$ | 2000 | | | V |
| C-E Breakdown Voltage | $V_{(BR)CEO}$ | $I_C = 100\mu A, R_{BE} = \infty$ | 1800 | | | V |
| E-B Breakdown Voltage | $V_{(BR)EBO}$ | $I_E = 10\mu A, I_C = 0$ | 5 | | | V |
| Output Capacitance | c_{ob} | $V_{CB} = 100V, f = 1MHz$ | | 1.4 | | pF |

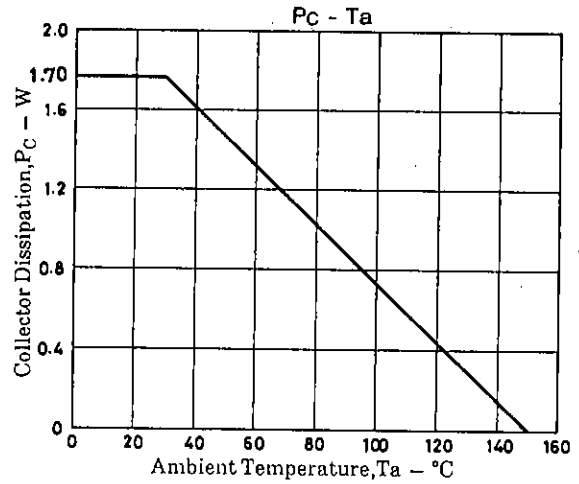
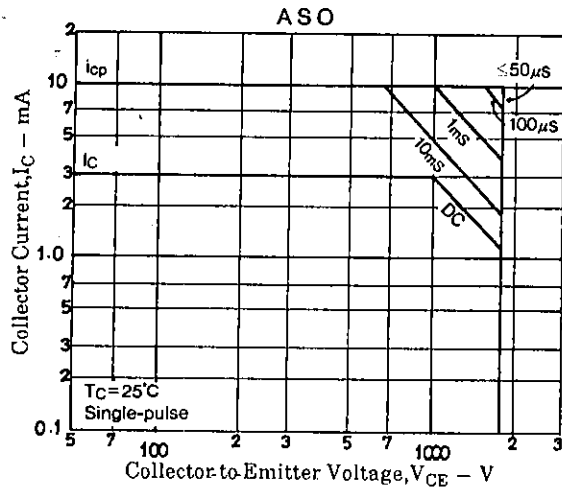
Package Dimensions 2010B

(unit: mm)



2SC4475





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